

Features

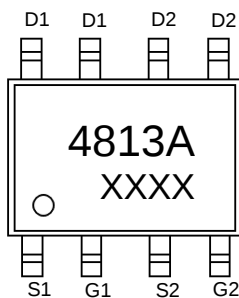
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	20m Ω @-10V	-7.1A
	30m Ω @-4.5V	

Application

- Battery protection
- Power management
- Load switch

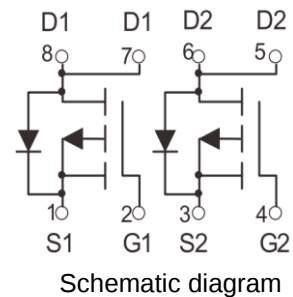


Marking and pin assignment

4813A : Device code
XXXX : Code



SOP-8 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-7.1	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	-40	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	-7.1	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	2	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		90	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MQ4813A	SOP-8	4813A	3,000	6,000	42,000	13"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-3.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-7.1A	--	20	25	mΩ
		V _{GS} =-4.5V, I _D =-5.6A	--	30	40	mΩ

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	1200	--	pF
C _{OSS}	Output Capacitance		--	155	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	135	--	pF

Switching Characteristics

Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-7.1A, V _{GS} =-10V	--	51	--	nC
Q _{gs}	Gate Source Charge		--	10	--	nC
Q _{gd}	Gate Drain Charge		--	8.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, I _D =-7.1A, V _{GS} =-10V, R _G =6Ω	--	13	--	nS
t _r	Turn-on Rise Time		--	15	--	nS
t _{d(off)}	Turn-Off Delay Time		--	200	--	nS
t _f	Turn-Off Fall Time		--	100	--	nS

Source- Drain Diode Characteristics

V _{SD}	Forward on voltage	T _J =25°C, I _S =-7.1A	--	-0.9	-1.2	V
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Typical Operating Characteristics

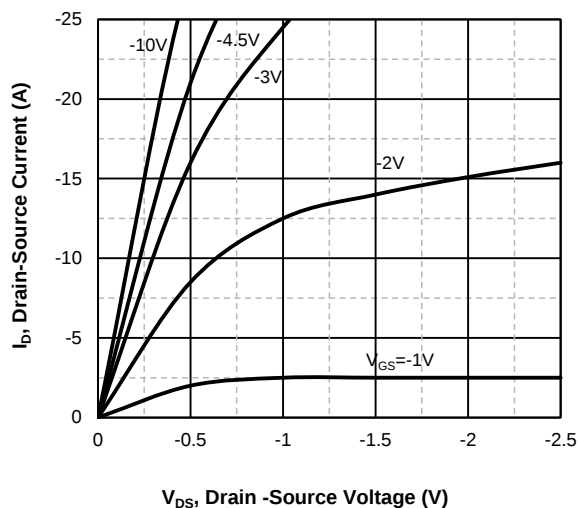


Fig1. Typical Output Characteristics

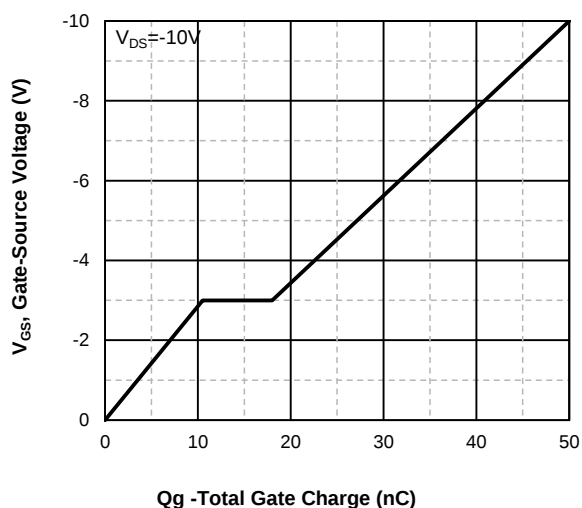


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

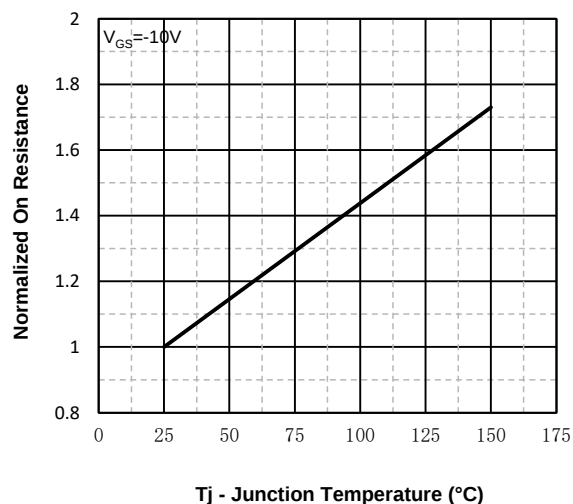


Fig3. Normalized On-Resistance Vs. Temperature

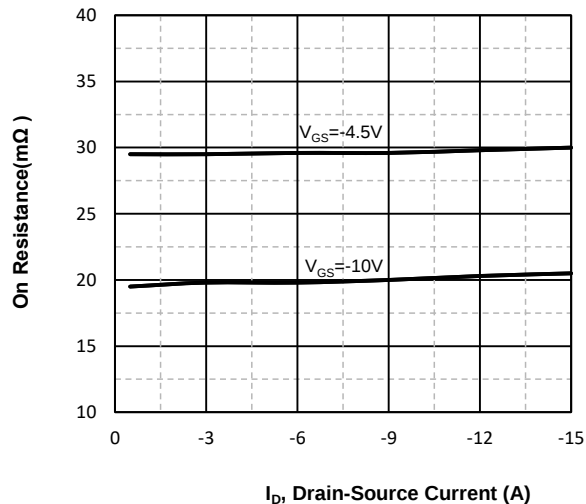


Fig4. On-Resistance Vs. Drain-Source Current

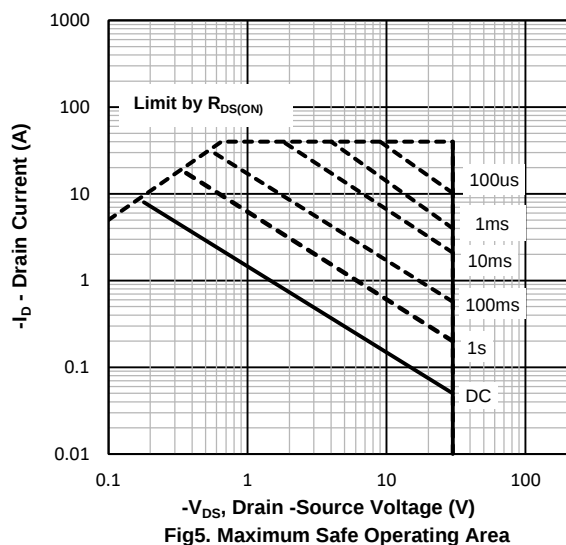


Fig5. Maximum Safe Operating Area

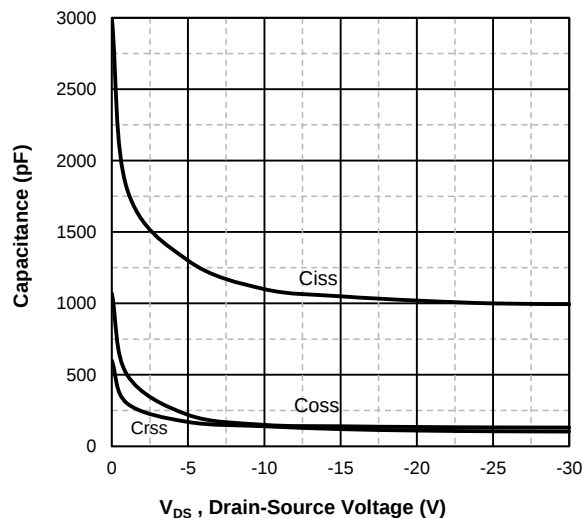


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°